

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.

## FAIRCHILD

SEMICONDUCTOR®

November 2013

## FQB47P06

## P-Channel QFET® MOSFET

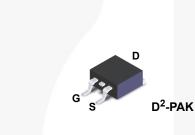
-60 V, -47 A, 26 mΩ

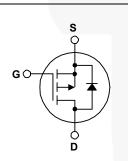
#### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### Features

- -47 A, -60 V,  $R_{DS(on)}$  = 26 m $\Omega$  (Max.) @ V<sub>GS</sub> = .10 V, I<sub>D</sub> = -23.5 A
- Low Gate Charge (Typ. 84 nC)
- Low Crss (Typ. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

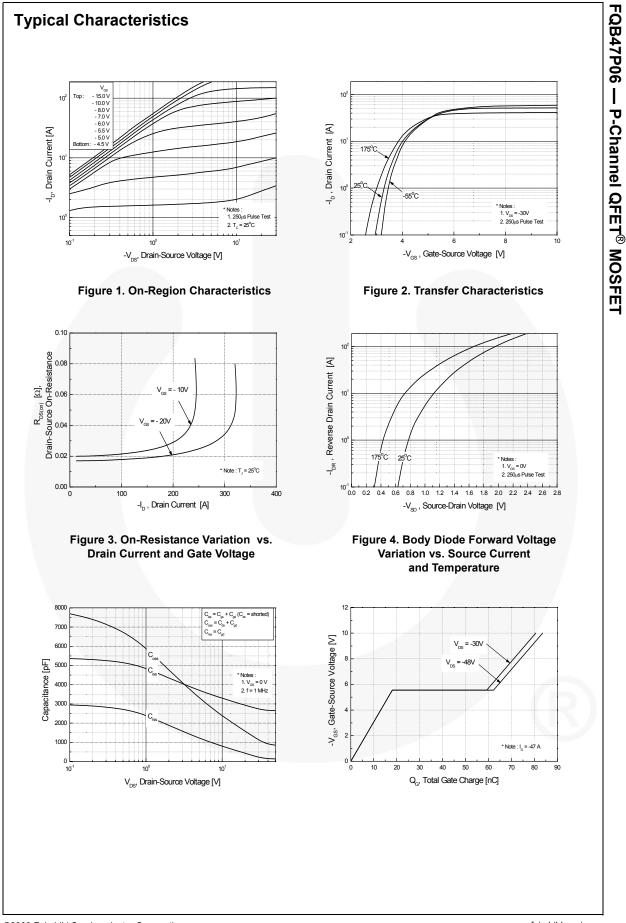
Symbol	Parameter		FQB47P06TM_AM002	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		-60	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		-47	А	
	- Continuous (T <sub>C</sub> = 100°C)		-33.2	A	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-188	A	
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		820	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	-47	А	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	16	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-7.0	V/ns	
P <sub>D</sub>	Power Dissipation $(T_A = 25^{\circ}C)^*$	3.75 W			
	Power Dissipation ( $T_C = 25^{\circ}C$ )	160	W		
	- Derate above 25°C		1.06	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C		
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C	

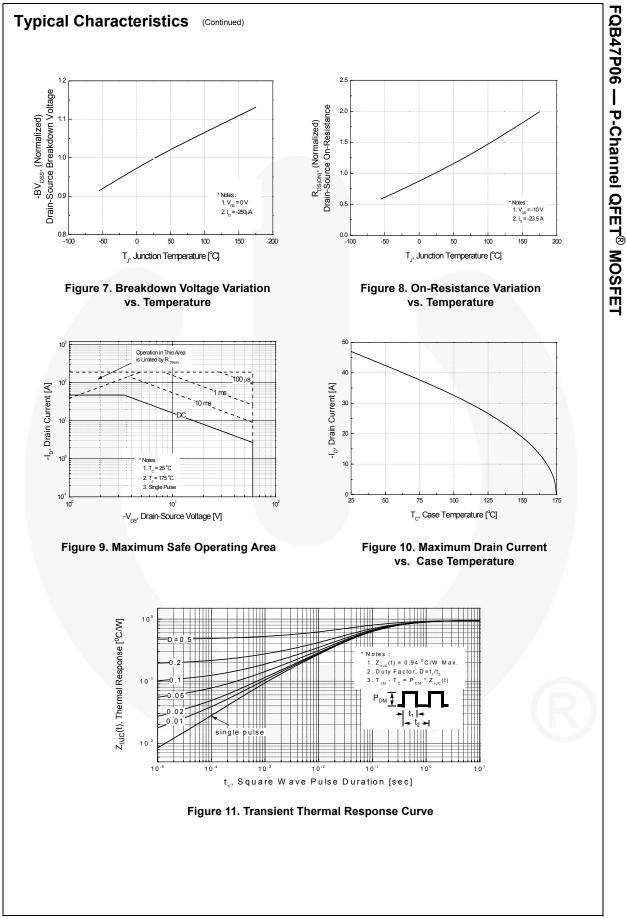
#### **Thermal Characteristics**

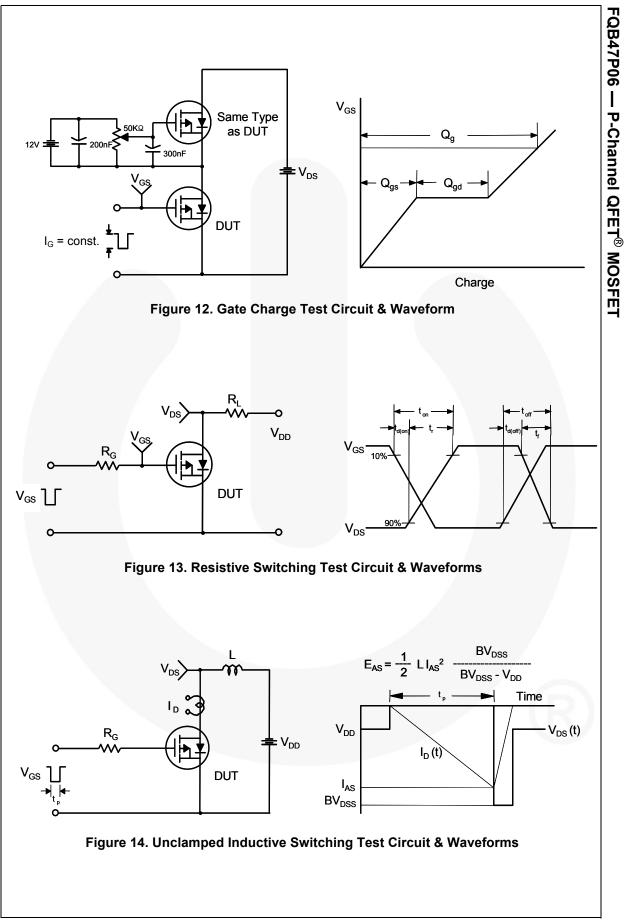
Symbol	Parameter	FQB47P06TM_AM002	02 Unit	
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	0.94		
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W	
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40		

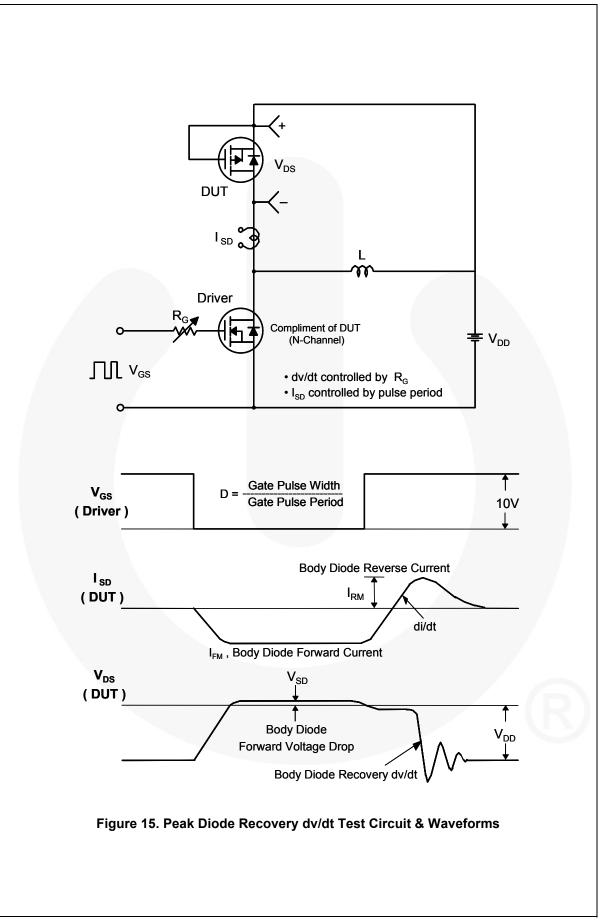
Part Number FQB47P06TM_AM002		Top Mark Pac		kage Packing Method Reel		Size	Tape Width		Quantity		
		FQB47P06	D <sup>2</sup> -	D <sup>2</sup> -PAK Tape and Reel 330		330	mm	24 mi	n	800 units	
lectri	cal Chara	cteristics	T <sub>C</sub> = 25°	C unless oth	herwise noted.						
Symbol		Parameter			Test Conditi	ons		Min.	Тур.	Max.	Unit
Off Cha	aracteristic	S									
3V <sub>DSS</sub>	DSS Breakdown Voltage Temperature		$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ $I_D = -250 \mu\text{A}, \text{ Referenced to } 25^{\circ}\text{C}$ $V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -48 \text{ V}, T_C = 150^{\circ}\text{C}$ $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$			-60			V		
∆BV <sub>DSS</sub> ′∆TJ							-0.06		V/°C		
DSS	Zero Gate Voltage Drain Current							-1 -10	μA μA		
I <sub>GSSF</sub> Gate-Body L		oakago Curront Forward						-100 -100 100	nA		
GSSF	Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse								nA		
				•65	201,105	•				100	
On Cha V <sub>GS(th)</sub>	Gate Thresh		-		V <sub>GS</sub> , I <sub>D</sub> = -250	Δ	_	-2.0		-4.0	V
GS(th)	Static Drain-S	Source		-	-10 V, I <sub>D</sub> = -23			-2.0	0.021	0.026	
9 <sub>FS</sub>		Forward Transconductance			-30 V, I <sub>D</sub> = -23.	5 A	-		21		S
9F5		isconductance	_	•DS	20.	071			21		5
Dynam	ic Characte	eristics									
C <sub>iss</sub>	Input Capaci	tance		$V_{DS} =$	-25 V, V <sub>GS</sub> = 0	V			2800	3600	pF
C <sub>oss</sub>	Output Capa	citance		f = 1.0		•,			1300	1700	pF
C <sub>rss</sub>	Reverse Tra	nsfer Capacitance							320	420	pF
Switchi	ing Charac	teristics									
d(on)	Turn-On Dela	ay Time		Vpp =	-30 V, I <sub>D</sub> = -23.	5 A.			50	110	ns
r	Turn-On Rise	e Time	_	$R_G = 2$	_	- ,			450	910	ns
d(off)	Turn-Off Dela	ay Time		Ŭ					100	210	ns
f	Turn-Off Fall	Time				(N	lote 4)		195	400	ns
ე <sub>g</sub>	Total Gate C	harge		V <sub>DS</sub> =	-48 V, I <sub>D</sub> = -47	A,			84	110	nC
Q <sub>gs</sub>	Gate-Source	Charge		V <sub>GS</sub> =	-10 V				18		nC
Q <sub>gd</sub>	Gate-Drain C	Charge				(N	lote 4)		44		nC
Drain-S	Source Dioc	le Characteris	stics a	nd Max	cimum Rati	ngs					
s	Maximum Co	ontinuous Drain-So	ource Dic	de Forw	ard Current					-47	А
SM	Maximum Pu	Ised Drain-Source	e Diode F	orward (	Current					-188	Α
V <sub>SD</sub>	Drain-Source	e Diode Forward V	/oltage	V <sub>GS</sub> =	0 V, I <sub>S</sub> = -47 A					-4.0	V
rr	Reverse Rec	overy Time			0 V, I <sub>S</sub> = -47 A,				130		ns
ວ <sub>rr</sub>	Reverse Rec	overy Charge		dl <sub>F</sub> / dt	: = 100 A/μs				0.55		μC
. L = 0.43 m . I <sub>SD</sub> ≤ -47 /	H, I <sub>AS</sub> = -47 A, V <sub>DD</sub> A, di/dt $\leq$ 300 A/µs	limited by maximum jun = -25 V, R <sub>G</sub> = 25 $\Omega$ , sta , V <sub>DD</sub> $\leq$ BV <sub>DSS</sub> , startin rrating temperature.	rting T <sub>J</sub> = 2	5°C.							

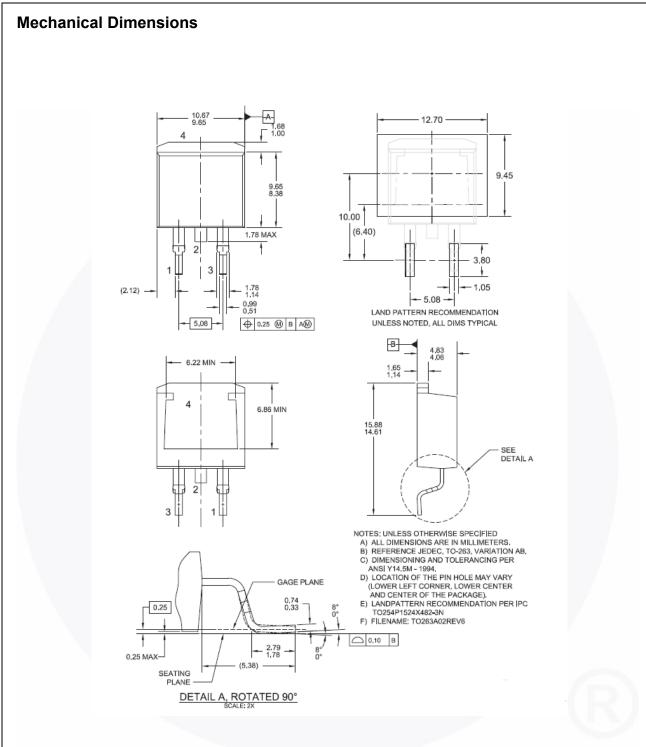
FQB47P06 — P-Channel QFET<sup>®</sup> MOSFET











#### Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT263-002

FQB47P06

- P-Channel QFET<sup>®</sup> MOSFET



No Identification Needed

Obsolete

notice to improve design.

**Full Production** 

Not In Production

Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.

Datasheet contains specifications on a product that is discontinued by Fairchild

Semiconductor. The datasheet is for reference information only.

Rev. 166

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC